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INFORMATION DISCLOSURE STATEMENT	Applicant Torston Wipiejewski et al-	
IN AN APPLICATION	Filing Date: November 26, 2003	Group Art Unic 2633

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*Substitute Disclosure Seatement Form (PTO-1449)

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^{*}Substitute Disclosure Statement Form (PTO-1449)

Date Faxed: March 28, 2005

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INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION U.S. PATENT DOCUMENTS U.S. PATENT DOCUMENTS Public 2883 Public 2883	Form 1449*				l n	locket Number: Clad. 12243-03-0	<u> </u>	Value of the state	HILDER TO/ /-	rzza i h	
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. IN AN APPLICATION	Filing Date: November 26, 2003	Group Art Unit 2883

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